# HARRIS HGTP14N40F3VL

Package

Symbol

COLLECTOR (FLANGE)

GATE O

# 14A, 400V N-Channel, Logic Level Voltage Clamping IGBT

JEDEC TO-220AB

COLLECTOR

EMITTER

GATE



### Features

- Logic Level Gate Drive
- Internal Voltage Clamp
- ESD Gate Protection
- T<sub>J</sub> = +150°C
- Ignition Energy Capable

## Applications

- · Automotive Ignition
- Small Engine Ignition
- Fuel Ignitor

## Description

This N-Channel IGBT is a MOS gated, logic level device which is intended to be used as an ignition coil driver in automotive ignition circuits. Unique features include an active voltage clamp between the drain and the gate and ESD protection for the logic level gate. Some specifications are unique to this automotive application and are intended to assure device survival in this harsh environment. The development type number for this device is TA49023.

#### PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND		
		2.0.012		
HGTP14N40F3VL	TO-220AB	14N40FVL		
NOTE: When ordering,	use the entire part numb	er.		

#### Absolute Maximum Ratings T<sub>C</sub> = +25°C, Unless Otherwise Specified

	HGTP14N40F3VL	UNITS
Collector-Emitter Breakdown Voltage at 10mA BV <sub>CES</sub>	420	V
Collector-Gate Breakdown Voltage $R_{GE} = 10k\Omega$ $BV_{CGR}$	420	V
Collector Current Continuous		
V <sub>GE</sub> = 4.5V at T <sub>C</sub> = +25 <sup>o</sup> CI <sub>C25</sub>	19	А
$V_{GE} = 4.5V$ at $T_{C} = +90^{\circ}C$ $I_{C90}$	14	А
Gate-Emitter Voltage Continuous V <sub>GES</sub>	±10	V
Gate-Emitter Voltage Pulsed or V <sub>GEM</sub>	±12	V
Gate-Emitter Current PulsedI <sub>GEM</sub>	±10	mA
Open Secondary Turn-Off Current		
L = 2.3mH at +25°C I <sub>CO</sub>	17	А
L = 2.3mH at +150°C	12	А
Drain to Source Avalanche Energy at L = 2.3mH, T <sub>C</sub> = +25 <sup>o</sup> C EAS	330	mJ
Power Dissipation Total at T <sub>C</sub> = +25 <sup>o</sup> CP <sub>T</sub>	83	W
Power Dissipation Derating $T_{C} > +25^{\circ}C$	0.67	W/ºC
Operating and Storage Junction Temperature Range	-40 to +150	°C
Maximum Lead Temperature for SolderingTL	260	°C
Electrostatic Voltage at 100pF, 1500ΩESD	6	KV

# HARRIS SEMICONDUCTOR IGBT PRODUCT IS COVERED BY ONE OR MORE OF THE FOLLOWING U.S. PATENTS:

4,364,073	4,417,385	4,430,792	4,443,931	4,466,176	4,516,143	4,532,534	4,567,641	
4,587,713	4,598,461	4,605,948	4,618,872	4,620,211	4,631,564	4,639,754	4,639,762	
4,641,162	4,644,637	4,682,195	4,684,413	4,694,313	4,717,679	4,743,952	4,783,690	
4,794,432	4,801,986	4,803,533	4,809,045	4,809,047	4,810,665	4,823,176	4,837,606	
4,860,080	4,883,767	4,888,627	4,890,143	4,901,127	4,904,609	4,933,740	4,963,951	
4.969.027			, ,	, ,	, ,	, ,	, ,	

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper ESD Handling Procedures. Copyright C Harris Corporation 1995

File Number 3407.2

	SYMBOL	TEST CONDITIONS		LIMITS			
PARAMETERS				MIN	ТҮР	МАХ	UNITS
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{\rm C} = 10 {\rm mA},$	T <sub>C</sub> = +150°C	345	370	415	V
		V <sub>GE</sub> = 0V	$T_{\rm C} = +25^{\rm o}{\rm C}$	350	375	420	V
			$T_{\rm C} = -40^{\rm o}{\rm C}$	355	380	425	V
Collector-Emitter Clamp Bkdn. Voltage	BV <sub>CE(CL)</sub>	I <sub>C</sub> = 10A	T <sub>C</sub> = +150°C	350	385	430	V
Emitter-Collector Breakdown Voltage	BV <sub>ECS</sub>	I <sub>C</sub> = 1.0mA	T <sub>C</sub> = +25 <sup>o</sup> C	24	-	-	V
Collector-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> = 250V	T <sub>C</sub> = +25 <sup>o</sup> C	-	-	50	μΑ
		V <sub>CE</sub> = 250V	T <sub>C</sub> = +150°C	-	-	250	μΑ
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> = 10A V <sub>GE</sub> = 4.5V	T <sub>C</sub> = +25 <sup>o</sup> C	-	-	2.0	V
			T <sub>C</sub> = +150 <sup>o</sup> C	-	-	2.3	V
Gate-Emitter Threshold Voltage	V <sub>GE(TH)</sub>	$I_{C} = 1.0 \text{mA}$ $V_{CE} = V_{GE}$	T <sub>C</sub> = +25°C	1.0	1.5	2.0	V
Gate-Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 10V$		-	-	±10	μΑ
Gate-Emitter Breakdown Voltage	BV <sub>GES</sub>	$I_{GES} = \pm 1.0 \text{mA}$		±12	-	-	V
Current Turn-off Time-Inductive Load	t <sub>D(OFF)</sub> I + t <sub>F(OFF)</sub> I	$ \begin{array}{l} {\sf R}_L = 32\Omega,  {\sf I}_C = 10{\sf A},  {\sf R}_G = 25\Omega, \\ {\sf L} = 550\mu{\sf H},  {\sf V}_{CL} = 320{\sf V},  {\sf V}_{GE} = 5{\sf V}, \\ {\sf T}_C = +125^o{\sf C} \end{array} $		-	12	16	μs
Inductive Use Test	UIS	L = 2.3 mH,	T <sub>C</sub> = +150°C	12	-	-	А
		v <sub>G</sub> = 5v, Figure 13	$T_{\rm C} = +25^{\rm o}{\rm C}$	17	-	-	А
Thermal Resistance	$R_{ extsf{ heta}JC}$		•	-	1.5	-	°C/W





## Test Circuits



FIGURE 13. USE TEST CIRCUIT

## Handling Precautions for IGBT's

Insulated Gate Bipolar Transistors are susceptible to gateinsulation damage by the electrostatic discharge of energy through the devices. When handling these devices, care should be exercised to assure that the static charge built in the handler's body capacitance is not discharged through the device. With proper handling and application procedures, however, IGBT's are currently being extensively used in production by numerous equipment manufacturers in military, industrial and consumer applications, with virtually no damage problems due to electrostatic discharge. IGBT's can be handled safely if the following basic precautions are taken:

 Prior to assembly into a circuit, all leads should be kept shorted together either by the use of metal shorting springs or by the insertion into conductive material such as "†ECCOSORBD LD26" or equivalent.





- 2. When devices are removed by hand from their carriers, the hand being used should be grounded by any suitable means for example, with a metallic wristband.
- 3. Tips of soldering irons should be grounded.
- 4. Devices should never be inserted into or removed from circuits with power on.
- 5. Gate Voltage Rating Never exceed the gate-voltage rating of  $V_{GEM}$ . Exceeding the rated  $V_{GE}$  can result in permanent damage to the oxide layer in the gate region.
- 6. **Gate Termination** The gates of these devices are essentially capacitors. Circuits that leave the gate opencircuited or floating should be avoided. These conditions can result in turn-on of the device due to voltage buildup on the input capacitor due to leakage currents or pickup.
- † Trademark Emerson and Cumming, Inc.